

FEATURES

- Qualified for Automotive Applications
- Low Power Consumption
- Wide Common-Mode and Differential Voltage Ranges
- Low Input Bias and Offset Currents
- Low Total Harmonic Distortion: 0.003% Typ
- High Input Impedance: JFET-Input Stage
- Latchup-Free Operation
- High Slew Rate: 13 V/µs Typ
- Common-Mode Input Voltage Range Includes V_{CC+}

DESCRIPTION/ORDERING INFORMATION

The TL082 JFET-input operational amplifier incorporates well-matched, high-voltage JFET and bipolar transistors in a monolithic integrated circuit. The device features high slew rates, low input bias and offset currents, and low offset-voltage temperature coefficient.

The I-suffix device is characterized for operation from -40° C to 85° C. The Q-suffix device is characterized for operation from -40° C to 125° C.

ORDERING INFORMATION⁽¹⁾

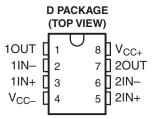
TJ	PACK	AGE ⁽²⁾	ORDERABLE PART NUMBER	TOP-SIDE MARKING
–40°C to 85°C	SOIC – D	Reel of 2500	TL082IDRQ1	TL082I
–40°C to 125°C	SOIC – D	Reel of 2500	TL082QDRQ1	TL082Q

(1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI web site at www.ti.com.

(2) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.

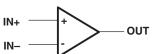


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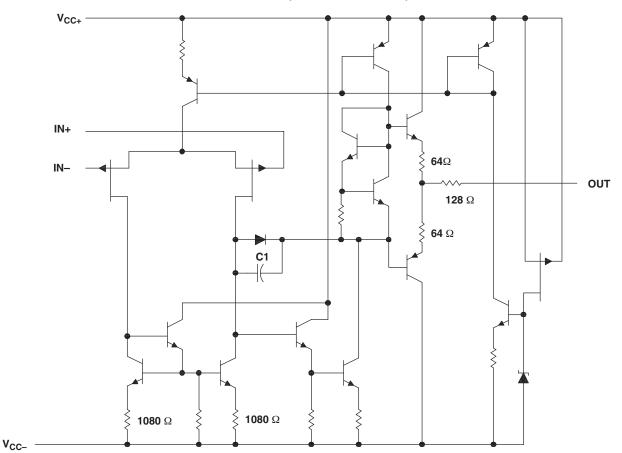




SYMBOL (EACH AMPLIFIER)



SCHEMATIC (EACH AMPLIFIER)



A. Component values shown are nominal.



ABSOLUTE MAXIMUM RATINGS⁽¹⁾

over operating free-air temperature range (unless otherwise noted)

			VALUE	
V_{CC+}	Supply voltage, positive ⁽²⁾		18 V	
V_{CC-}	Supply voltage, negative ⁽²⁾	-18 V		
V_{ID}	Differential input voltage ⁽³⁾	±30 V		
VI	Input voltage ⁽²⁾⁽⁴⁾	±15 V		
	Duration of output short circuit ⁽⁵⁾		Unlimited	
	Continuous total power dissipation		(6)	
H		TL082I	-40°C to 85°C	
T _A	Operating free-air temperature range	TL082Q	-40°C to 125°C	
θ_{JA}	Package thermal impedance, junction to free air ⁽⁷⁾	I	97°C/W	
		Human-Body Model	1.5 kV (H1C)	
	ESD rating ⁽⁸⁾	Charged-Device Model	1.5 kV (C5)	
		Machine Model	200 V (M3)	
	Operating virtual junction temperature	· · ·	150°C	
T _{stg}	Storage temperature range		–65°C to 150°C	

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltage values, except differential voltages, are with respect to the midpoint between V_{CC+} and V_{CC-} .

(3) Differential voltages are at IN+ with respect to IN-.

(4) The magnitude of the input voltage must never exceed the magnitude of the supply voltage or 15 V, whichever is less.

(5) The output may be shorted to ground or to either supply. Temperature and/or supply voltages must be limited to ensure that the dissipation rating is not exceeded.

(6) Maximum power dissipation is a function of $T_J(max)$, θ_{JA} , and T_A . The maximum allowable power dissipation at any allowable ambient temperature is PD = $(T_J(max) - T_A)/\theta_{JA}$. Operating at the absolute maximum T_J of 150°C can affect reliability.

(7) The package thermal impedance is calculated in accordance with JESD 51-7.

(8) ESD protection level per JEDEC classifications JESD22-A114 (HBM), JESD22-A115 (MM), and JESD22-C101 (CDM).

TL082-Q1 JFET-INPUT OPERATIONAL AMPLIFIER

SLOS548-SEPTEMBER 2007



ELECTRICAL CHARACTERISTICS⁽¹⁾

 $V_{CC+} = \pm 15 V$ (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	T _A ⁽²⁾	MIN	TYP	MAX	UNIT
V _{IO} Input offset voltage		$V_{2} = 0$ $P_{2} = 50.0$	25°C		3	6	mV
V _{IO}	Input onset voltage	$V_{O} = 0, R_{S} = 50 \Omega$	Full range			9	mv
α_{VIO}	Temperature coefficient of input offset voltage	$V_O = 0, R_S = 50 \ \Omega$	Full range		18		µV/∘C
1	Input offset current ⁽³⁾	V = 0	25°C		5	100	pА
I _{IO}	input onset current of	$V_{O} = 0$	Full range			20	nA
	Input bias current ⁽³⁾	$V_{\Omega} = 0$	25°C		30	200	pА
I _{IB}		$v_{O} = 0$	Full range			50	nA
V _{ICR}	Common-mode input voltage range		25°C	±11	–12 to 15		V
		$R_L = 10 \text{ k}\Omega$	25°C	±12	±13.5		V
V _{OM}	Maximum peak output voltage swing	R _L ≥ 10 kΩ	Eull rongo	±12			
		$R_{L} \ge 2 k\Omega$ Full range		±10	±12		
Large-signal differential voltage		$V_{\Omega} = \pm 10 \text{ V}, \text{ R}_{I} \geq 2 \text{ k}\Omega$	25°C	50	200		\//m\/
A _{VD}	amplification	$v_0 = \pm 10 v, R_1 \ge 2 R_{22}$	Full range	15			V/mV
B1	Unity-gain bandwidth		25°C		3		MHz
r _i	Input resistance		25°C		10 ¹²		Ω
CMRR	Common-mode rejection ratio	$V_{IC} = V_{ICR}(min), V_O = 0, R_S = 50 \ \Omega$	25°C	75	86		dB
k _{SVR}	Supply-voltage rejection ratio $(\Delta V_{CC\pm}/\Delta V_{IO})$	$\begin{array}{l} V_{CC} = \pm 15 \text{ V to } \pm 9 \text{ V}, \\ V_O = 0, \text{ R}_S = 50 \Omega \end{array}$	25°C	80	86		dB
I _{CC}	Supply current (per amplifier)	$V_{O} = 0$, No load	25°C		1.4	2.8	mA
V ₀₁ /V ₀₂	Crosstalk attenuation	A _{VD} = 100	25°C		120		dB

(1) All characteristics are measured under open-loop conditions with zero common-mode voltage, unless otherwise specified. (2) Full range for T_A is -40°C to 85°C for I-suffix devices and -40°C to 125°C for Q-suffix devices.

(2) (3) Input bias currents of an FET-input operational amplifier are normal junction reverse currents, which are temperature sensitive, as shown in Figure 14. Pulse techniques must be used that maintain the junction temperature as close to the ambient temperature as possible.

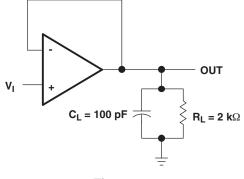
OPERATING CHARACTERISTICS

 $V_{CC\pm} = \pm 15 \text{ V}, \text{ T}_{\text{A}} = 25^{\circ}\text{C}$ (unless otherwise noted)

	PARAMETER	TEST CO	MIN	TYP	MAX	UNIT	
SR	Slew rate at unity gain	$V_{I} = 10 \text{ V}, \text{ R}_{L} = 2 \text{ k}\Omega, \text{ C}_{L} =$	100 pF, See Figure 1	8	13		V/µs
t _r	Rise time	V_{I} = 20 mV, R_{L} = 2 k Ω , C_{L}	= 100 pF, See Figure 1		0.05		μs
	Overshoot factor	V_{I} = 20 mV, R_{L} = 2 k Ω , C_{L}		20		%	
V _n E		D 00 0	f = 1 kHz		18		nV/√Hz
	Equivalent input noise voltage	R _S = 20 Ω		4		μV	
I _n	Equivalent input noise current	$R_S = 20 \Omega$, f = 1 kHz		0.01		pA/√ Hz	
THD	Total harmonic distortion	V _{Irms} = 6 V, f = 1 kHz, AVD	= 1, $R_S \le 1 \text{ k}\Omega$, $R_L \ge 2 \text{ k}\Omega$		0.003		%



PARAMETER MEASUREMENT INFORMATION





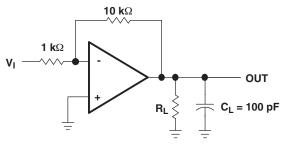


Figure 2.

TL082-Q1 JFET-INPUT OPERATIONAL AMPLIFIER



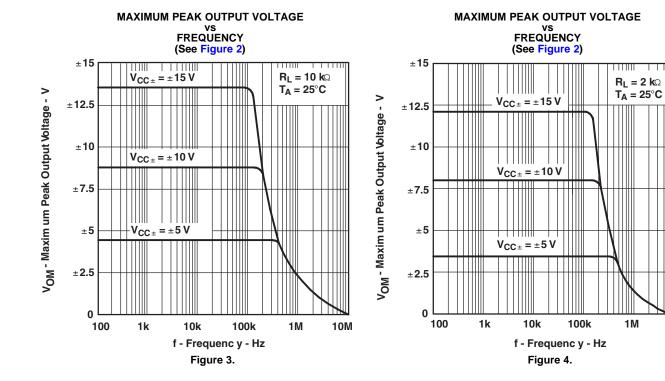
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TYPICAL CHARACTERISTICS

Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the devices.

Table	of	Graphs
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			FIGURE
		vs Frequency	3, 4, 5
V _{OM}		vs Free-air temperature	6
	Maximum peak output voltage	vs Load resistance	7
		vs Supply voltage	8
٨		vs Free-air temperature	9
A _{VD}	Large-signal differential voltage amplification	vs Frequency	10
PD	Total power dissipation	vs Free-air temperature	11
	Currentu current	vs Free-air temperature	12
I _{CC}	Supply current	vs Supply voltage	13
I _{IB}	Input bias current	vs Free-air temperature	14
	Large-signal pulse response	vs Time	15
Vo	Output voltage	vs Elapsed time	16
CMRR	Common-mode rejection ratio	vs Free-air temperature	17
V _n	Equivalent input noise voltage	vs Frequency	18
THD	Total harmonic distortion	vs Frequency	19



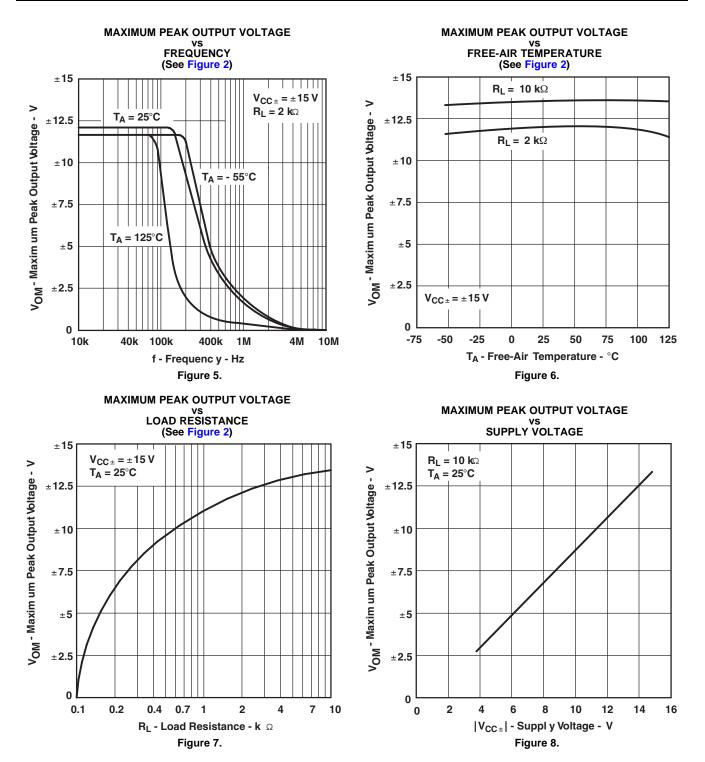
6

10M

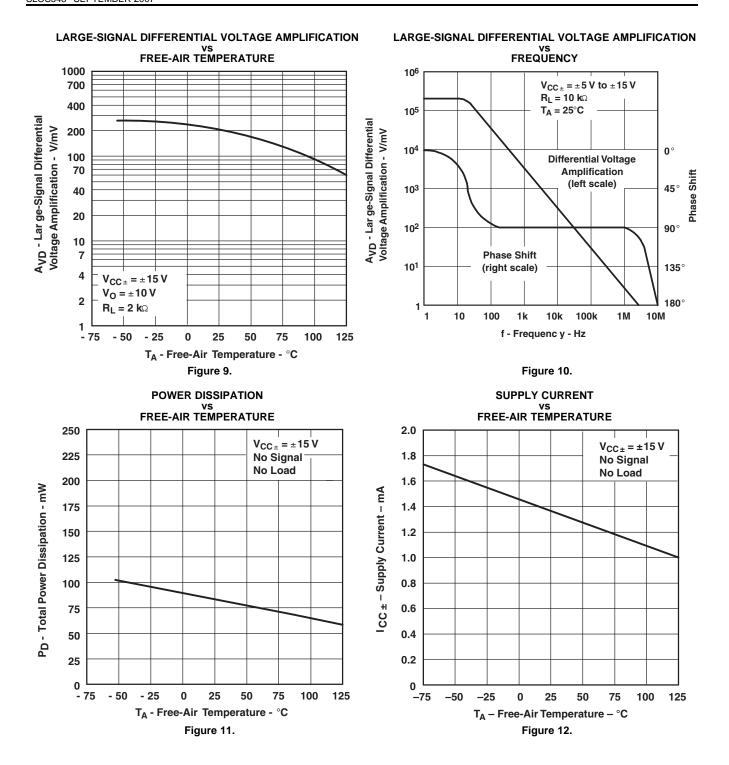
1M



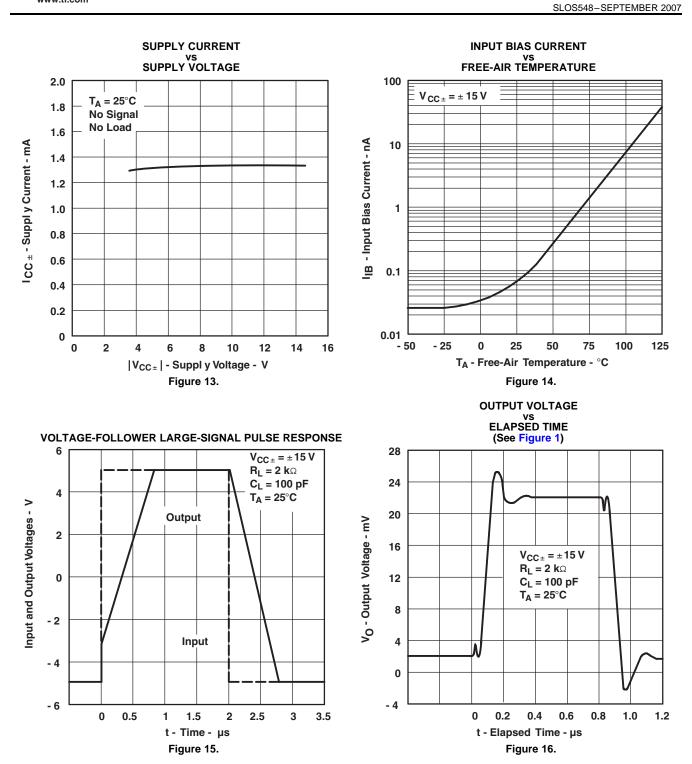
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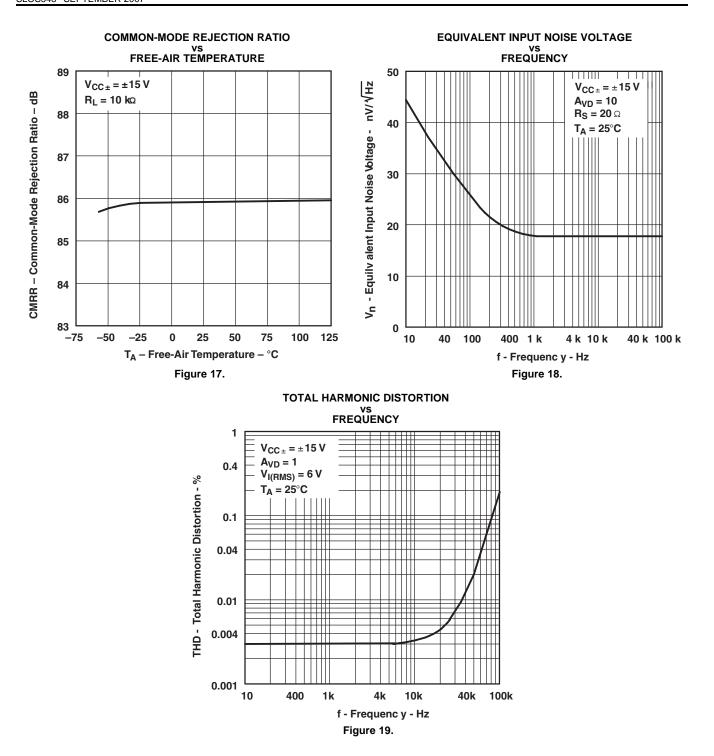






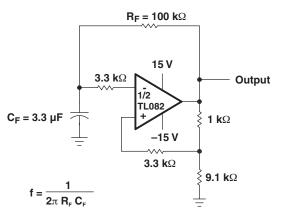
TL082-Q1 JFET-INPUT OPERATIONAL AMPLIFIER SLOS548-SEPTEMBER 2007



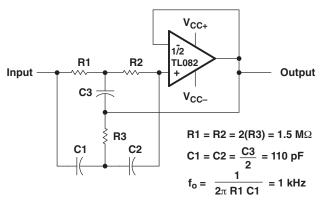




APPLICATION INFORMATION









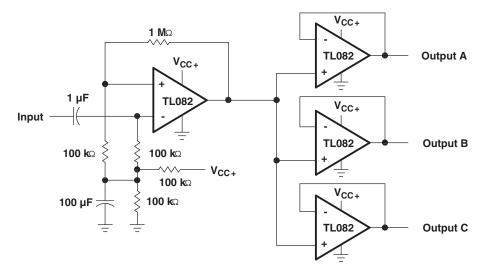
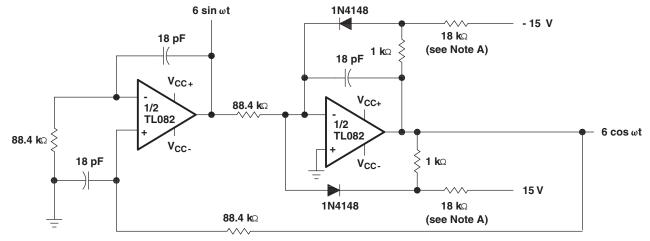


Figure 22. Audio-Distribution Amplifier

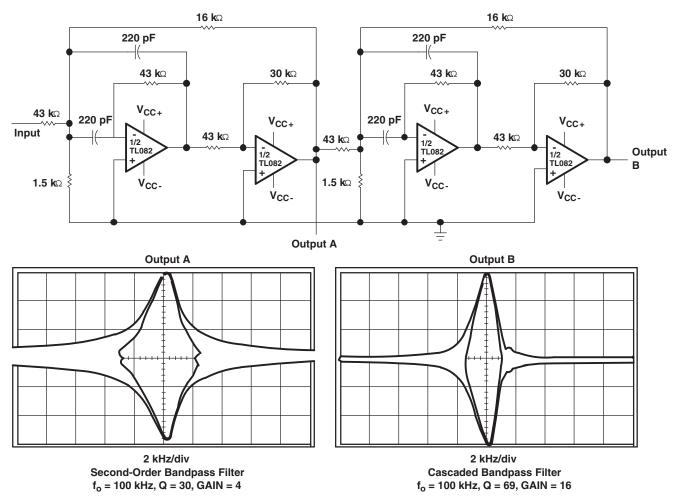
TL082-Q1 JFET-INPUT OPERATIONAL AMPLIFIER SLOS548-SEPTEMBER 2007

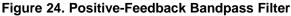




A. These resistor values may be adjusted for a symmetrical output.









11-Apr-2013

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Top-Side Markings	Samples
	(1)		Drawing		Qty	(2)		(3)		(4)	
TL082IDRQ1	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TL0821	Samples
TL082QDRQ1	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	TL082Q	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between

the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) Multiple Top-Side Markings will be inside parentheses. Only one Top-Side Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Top-Side Marking for that device.

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OTHER QUALIFIED VERSIONS OF TL082-Q1 :



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PACKAGE OPTION ADDENDUM

11-Apr-2013

Catalog: TL082

Military: TL082M

NOTE: Qualified Version Definitions:

- Catalog TI's standard catalog product
- Military QML certified for Military and Defense Applications

D0008A



PACKAGE OUTLINE

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES:

1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.

- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.
- 5. Reference JEDEC registration MS-012, variation AA.



D0008A

EXAMPLE BOARD LAYOUT

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



D0008A

EXAMPLE STENCIL DESIGN

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

9. Board assembly site may have different recommendations for stencil design.



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